

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

2SK3471

Switching Regulator and DC-DC Converter Applications

- Low drain-source ON-resistance: $R_{DS(ON)} = 10\ \Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 0.4\ \text{S}$ (typ.)
- Low leakage current: $I_{DSS} = 100\ \mu\text{A}$ (max) ($V_{DS} = 500\ \text{V}$)
- Enhancement model: $V_{th} = 2.0$ to $4.0\ \text{V}$ ($V_{DS} = 10\ \text{V}$, $I_D = 1\ \text{mA}$)

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	500	V
Drain-gate voltage ($R_{GS} = 20\ \text{k}\Omega$)		V_{DGR}	500	V
Gate-source voltage		V_{GSS}	± 30	V
Drain current	DC (Note 1)	I_D	0.5	A
	Pulse (Note 1)	I_{DP}	1.5	
Drain power dissipation		P_D	0.5	W
Drain power dissipation (Note 2)		P_D	1.5	W
Single pulse avalanche energy (Note 3)		E_{AS}	14.3	mJ
Avalanche current		I_{AR}	0.5	A
Repetitive avalanche energy (Note 4)		E_{AR}	0.05	mJ
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	-55 to 150	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	250	$^\circ\text{C/W}$

Note 1: Ensure that the channel temperature does not exceed 150°C

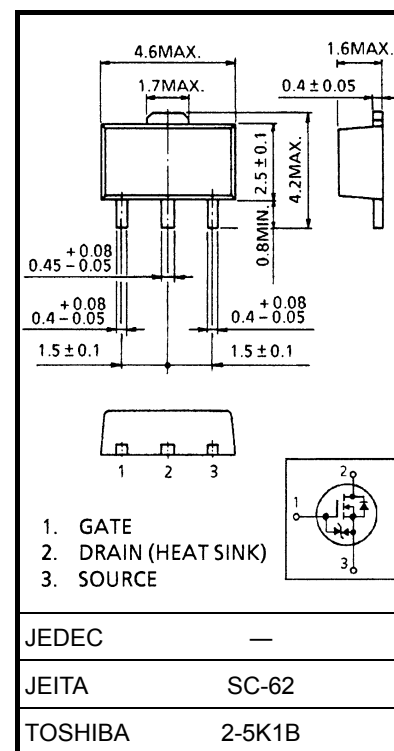
Note 2: Mounted on a ceramic substrate ($25.4\ \text{mm} \times 25.4\ \text{mm} \times 0.8\ \text{mm}$)

Note 3: $V_{DD} = 90\ \text{V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 100\ \text{mH}$, $R_G = 25\ \Omega$, $I_{AR} = 0.5\ \text{A}$

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

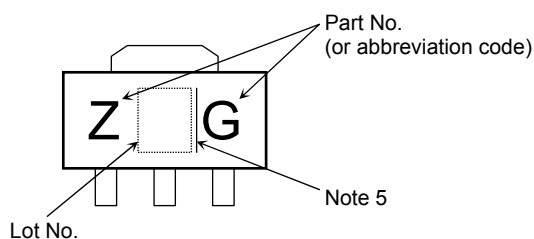
This transistor is an electrostatic-sensitive device. Please handle with caution.

Unit: mm



Weight: 0.05 g (typ.)

Marking



Note 5: A line beside a Lot No. identifies the indication of product Labels.

Without a line: [[Pb]]/INCLUDES > MCV

With a line: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 10	μA
Gate-source breakdown voltage		$V_{(BR)GSS}$	$I_G = \pm 10 \mu\text{A}, V_{DS} = 0 \text{ V}$	± 30	—	—	V
Drain cut-OFF current		I_{DSS}	$V_{DS} = 500 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	100	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	500	—	—	V
Gate threshold voltage		V_{th}	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	2.0	—	4.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10 \text{ V}, I_D = 0.25 \text{ A}$	—	10	18	Ω
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10 \text{ V}, I_D = 0.25 \text{ A}$	0.2	0.4	—	S
Input capacitance		C_{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	75	—	pF
Reverse transfer capacitance		C_{rss}		—	7	—	
Output capacitance		C_{oss}		—	24	—	
Switching time	Rise time	t_r		—	11	—	ns
	Turn-ON time	t_{on}		—	18	—	
	Fall time	t_f		—	54	—	
	Turn-OFF time	t_{off}		—	95	—	
Total gate charge (gate-source plus gate-drain)		Q_g	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 0.5 \text{ A}$	—	3.8	—	nC
Gate-source charge		Q_{gs}		—	1.9	—	
Gate-drain ("miller") charge		Q_{gd}		—	1.9	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	0.5	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	1.5	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = 0.5 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-1.5	V
Reverse recovery time	t_{rr}	$I_{DR} = 0.5 \text{ A}, V_{GS} = 0 \text{ V},$	—	190	—	ns
Reverse recovery charge	Q_{rr}	$dI_{DR}/dt = 100 \text{ A} / \mu\text{s}$	—	380	—	nC

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